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Kind regards,

Team Nexperia

1. General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540X.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

3. Applications

- · Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch mode power supply

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	-500	V
V _{CEO}	collector-emitter voltage	open base	-	-	-400	V
I _C	collector current		-	-	-0.25	Α
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -50 mA; T_{amb} = 25 °C	100	200	-	





500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		2
2	С	collector		3—
3	В	base	3 2 1 SOT89	1 sym079

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV9040X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

7. Marking

Table 4. Marking codes

	Table 4. Marking Socio					
Type number		Marking code				
		[1]				
	PBHV9040X	%4E				

[1] % = placeholder for manufacturing site code

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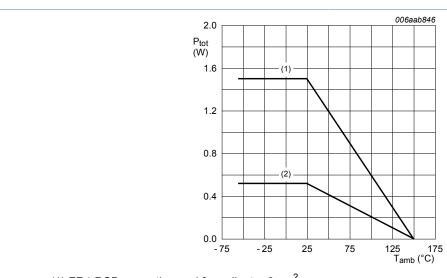
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-500	V
V _{CEO}	collector-emitter voltage	open base		-	-400	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-500	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-0.25	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-0.5	Α
I _{BM}	peak base current			-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.52	W
			<u>[2]</u>	-	1.5	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

PBHV9040X

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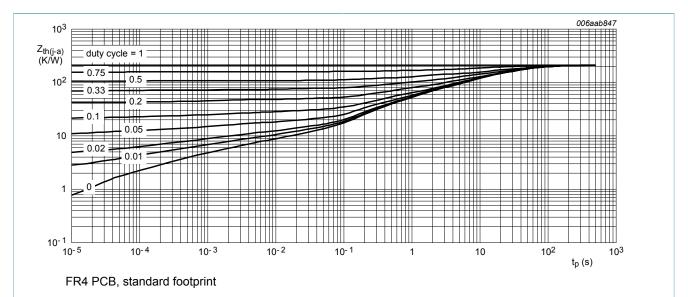
Thermal characteristics

Table 6. Thermal characteristics

PBHV9040X

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
(2)	thermal resistance from junction to ambient	in free air	[1]	-	-	240	K/W
			[2]	-	-	83	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.

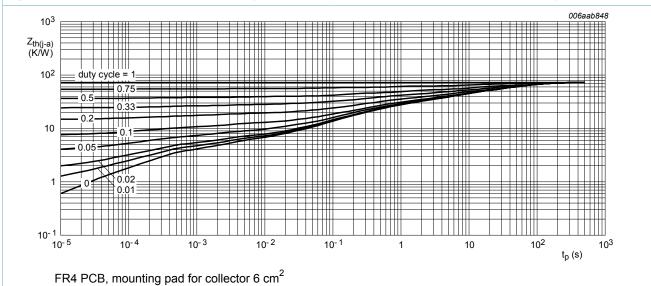


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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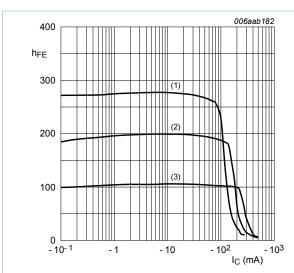
500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -320 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -320 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -320 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -50 mA; T_{amb} = 25 °C	100	200	-	
		$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ $T_{amb} = 25 \text{ °C}$	80	200	-	
		V_{CE} = -10 V; I_{C} = -250 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	10	25	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -100 mA; I_B = -20 mA; T_{amb} = 25 °C	-	-110	-200	mV
V _{BEsat}	base-emitter saturation voltage	I_{C} = -100 mA; I_{B} = -20 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-1	-1.1	V
t _d	delay time	V _{CC} = -2 V; I _C = -0.15 A; I _{Bon} = -0.03 A;	-	9	-	ns
t _r	rise time	I _{Boff} = 0.03 A; T _{amb} = 25 °C	-	1810	-	ns
t _{on}	turn-on time		-	1819	-	ns
t _s	storage time		-	715	-	ns
t _f	fall time		-	1085	-	ns
t _{off}	turn-off time		-	1800	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	-	55	-	MHz
C _c	collector capacitance	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	7	-	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f_{c} = 1 MHz; f_{amb} = 25 °C	-	150	-	pF

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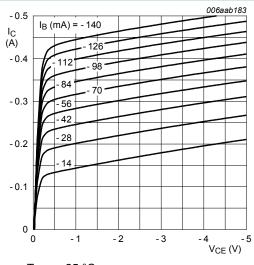
$$V_{CE}$$
 = -10 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

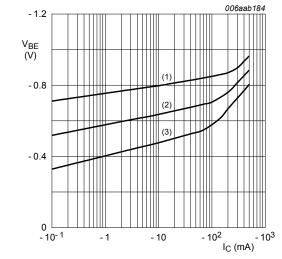
$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



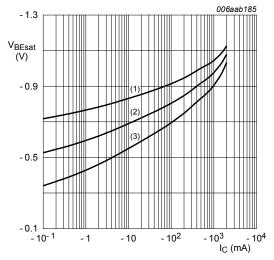
$$V_{CE}$$
 = -10 V

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

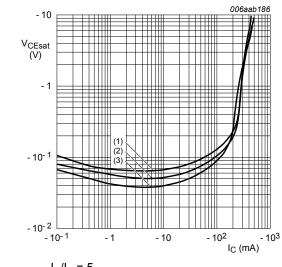
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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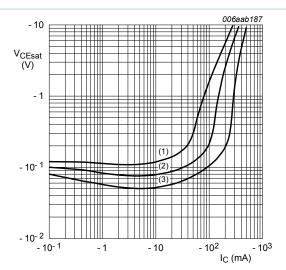
$$I_{\rm C}/I_{\rm B} = 5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



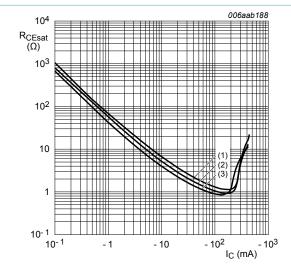
$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



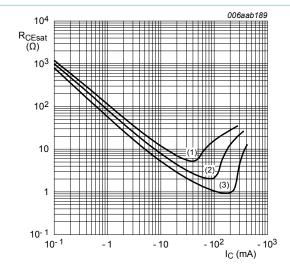
$$I_C/I_B = 5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

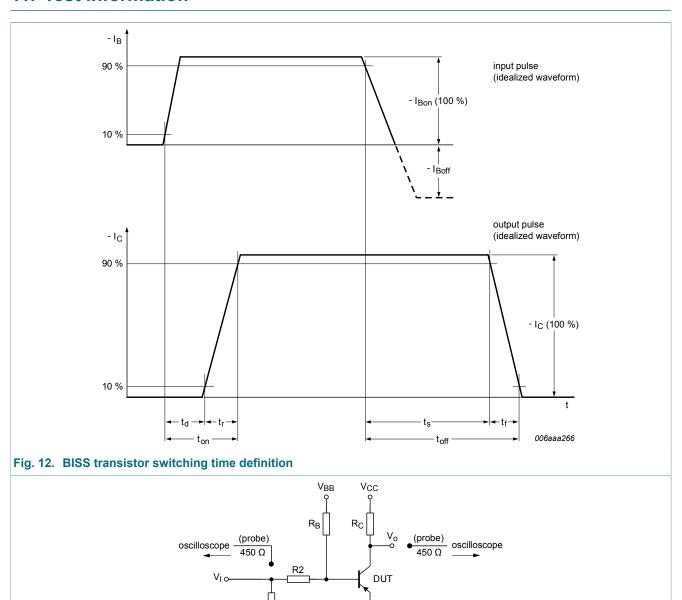
(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



11.1 Quality information

Fig. 13. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

mgd624

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12. Package outline

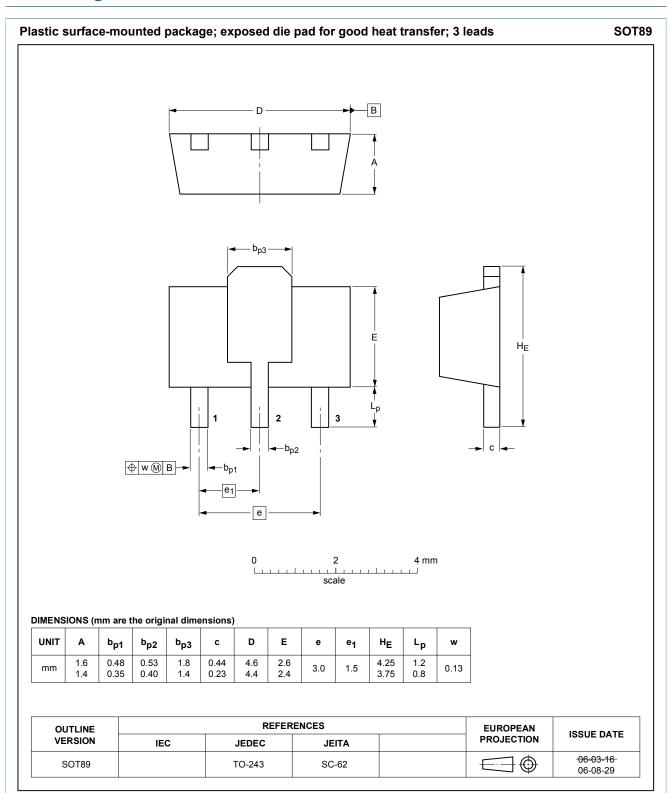
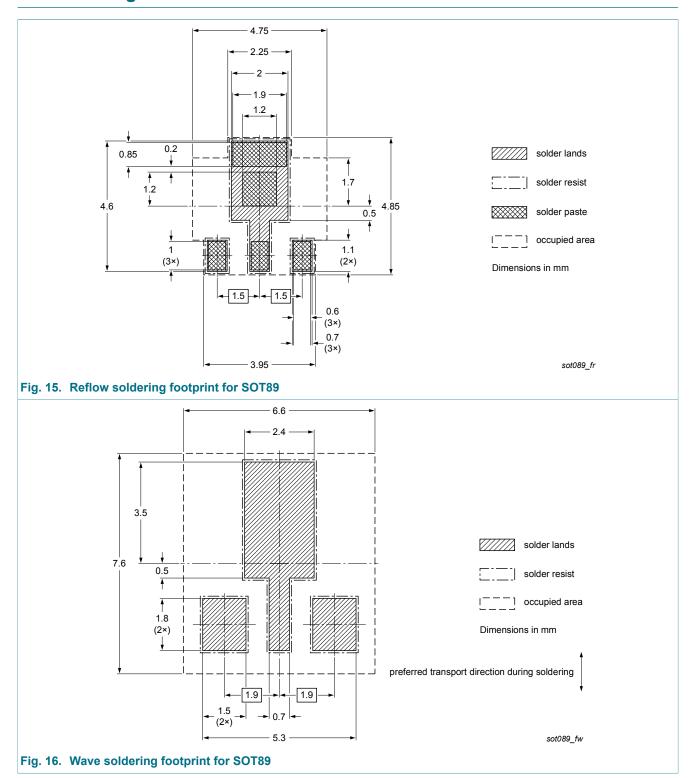


Fig. 14. Package outline SOT89

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9040X v.1	20131209	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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